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This paper gives a summary on the properties of polyimide films used in microelectronic devices and on recent research efforts to understand the adhesion between polyimides and inorganic materials. One of the major concerns in the application of polyimides is the integrity and reliability of the laminar structures. Surface sensitive spectroscopies have been recently applied to identify the nature of the chemical bond for metals evaporated onto cured polyimide surfaces and for spun-on and subsequently imidized polyamic acid films on metal surfaces. Depending on the preparation of the interface, e.g. metal on polymer or polymer on bulk metal, different phenomena are observed.

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Properties and Adhesion of Polyimides in Microelectronic

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PDSTract

This paper gives a summary on the properties of polyimide films used in microelectronic devices and on recent research efforts to understand the adhesion between polyimides and inorganic materials. One of the major concerns in the application of polyimides is the integrity and reliability of the laminar structures. Surface sensitive spectroscopies have been recently applied to identify the nature of the chemical bond for metals evaporated onto cured polyimide surfaces and for spun-on and subsequently imidized polyamic acid films on metal surfaces. Depending on the preparation of the interface, e.g. metal on polymer or polymer on bulk metal, different phenomena are ob-

The widespread use of polyimides (PI) is a result of their unique properties which can be tailored to fulfill or to provide a compromise for specific requirements. Aromatic linear polyimides in particular are a class of organic polymers with favourable mechanical and delectric properties for applications in electronic devices which can easily be processed into planar films. Originally polyimides were introduced in Japan as an interlevel delectric for multilevel metal translators /1/. Today they are used routinely in VLSI devices as multilevel dielectric insulation /2-4/. There are also several other applications which emerged in the last 10-15 years. Because of their high absorption coefficient for α -particles they are used as protective coatings in charge sensitive memory devices, their mechanical properties and high temperature stability is utilized in composite materials for aerosyace uses /5/, and they are tested as high temperature adhesives /6/ as well as lubricants in spacecraft applications ///. More recent application of some polyimides take advantage of their crystallinity which makes them applicable as orienting layers for LCD devices, or, when crystallization is reduced by adjustment of the curing procedure, as light. guide materials /8/.

ments, remains to be a major issue of concern in the application of PI's. Only recently spectroscopic results on polyimide/metal interfaces have become available which can shed some light on the chemical and physical parameters determining the adhesive bond between polyimide and metallic, oxidic, or semiconducting substrates. These experi-However, reliable adhesion, particular in humid environ-

ments will be summarized in the second part of this paper.

1) Preparation and Properties of Aromatic Polyimides

action of an aromatic tetracarboxylic diamhydride and an aromatic diamine. In the two-step reaction a soluble, polyamic acid is formed which can be converted to polyimide by thermal or chemical loss of water. To date nearly every aromatic and aliphatic function in the diamhydride or diaphysical properties of the polymer over a wide range. A physical properties of the polymer over a wide range. A chemical stability, thermal stability, optical, electrical and mechanical properties as a function of the relationship between ture can be found in the monograph "Polyimides: Thermally with rivid rod-like structures (e.g. p-phenylene pyromeiltimide, show the highest thermal stability, followed by polyimides of rigid cyclic structures of the ladder type and those containing single "hinge" atoms between the phenyl rings in the diamine, e.g. poly (N.N.) - (phenoxyphenyl) - pyromeiltimide (PMDA/ODA). The thermal stability of the macro-molecule interactions and note by the flexibility of the macro-molecules therewise the macro-Aromatic polyimides can be prepared by a condensation remolecules themselves /9/.

pansion-coefficient of quartz glass (4 x 10⁻⁷K⁻¹), ceramics, metals and on the higher end those of ordinary ortween thermal expansion and chemical structure are discussed by Numata et al. (10/. Numata et al. (10/also describe the use of low thermal expansion coefficient polylmides as interlayer dielectric in VLSI's and flexible printed circuit boards. The matched thermal expansion coefficient of the dielectric polylmide film to the metallication layers or inorganic substrates in the laminar structure is essential because the device has to withstand the anneal temperature and further thermal cycling, e.g. The physical reason for the high flexibility of polyimides is a high degree of freedom of rotation of the phenylene rings around internal atomic "hinges" in the diamine portion of the polymer. The thermal expansion coefficients can be controlled by the chemical composition from 4 x 10^{-7} to 5.7 x $10^{-5}\mathrm{K}^{-1}$ /10/, hence matching the thermal exin soldering processes.

romellitimides have been investigated and it was observed that the high temperature conductivity (T>230°C) correlates with the ionisation potential and electron affinities of the electron donor (diamine) and electron acceptor (dianhydride) units in the chain The electrical conductivity increases sharply upon illumination with visible The dark and photoelectric conductivity of various polypy-

light by about a factor of 100 at room temperature /9/. In terms of dielectric properties, aromatic polyimides are classified as medium frequency dielectrics with a dielectric constant of typically ϵ -3.0-3.8, dielectric breakdown strengths of 100-200 mV/m, and a specific volume resistance of -10¹⁸ Ω cm. The parameters remain nearly independent of fiequency and temperature up to -200°C thus making them an ideal choice for a dielectric in heat resistant electrical insulating laminar structures.

The same that the same

Exposure to moisture at elevated temperature leads to water absorption in the polyimide film /11,12/. As discussed by Wilson /11/, water absorption (up to 1.5 H₂O molecules per repeat unit) is believed to hydrolyse polyimide to polyamic acid. Subsequent annealing up to 450°C in nitrogen for 30 minutes removes the water. Water absorption leads to a tensile stress in the polymer film which cause delamination, in particular in cases where the film is not coupled to the substrate (SiO₂) by an adhesion promoter, e.g. organosilanes /11/. In order to avoid moisture induced degradation, polyimide films used as passivation coatings are typically covered with another plastic passivant /11/ as a moisture barrier.

Although the macroscopic behavior of polyimide films degraded by moisture exposure has been well established, the chemical changes occurring in the interface leading to admessive or cohesive failure of the laminar structure are not well understood. Basically, in order to describe the failure mechanism, the chemical interactions and the structural properties of the intact interface need to be known. The present understanding of the chemical and physical interactions between polyimide and inorganic films is summarized in the following paragraphs.

2) Chemical interactions in polyimida/metal interfaces

Experiments to determine the chemical interaction between polyimide and metals have concentrated on poly [N,N'-| phenoxyphenyl)-pyromellitimide (PMDA-ODA) and related model compounds. The two methods to prepare PMDA-ODA polyimide films are spin coating (SC) and vapor deposition polymerisation (VDP). They differ in the way the film precursor (polyamic acid) is applied to the substrate. VDP is a solventless technique in which the monomers PMDA and ODA are codeposited by evaporation onto the substrate where they react at room temperature to polyamic acid. Spin coating (SC) requires that the polymer precursor polyamic acid is applied in a polar solvent, typically N-methyl pyrolidone (NMP). The interfacial chemistry and adhesion is directly influenced by the way in which the interface is formed. Therefore, variations in the preparation of the polymer and/or metal film will lead to polyimide/metal interfaces with different physiochemical properties.

In the following the results obtained for the interfacial

chemistry of metals deposited onto cured polyimide, spin coated polyimide on metals and silicon, and for vapor deposited polyimide films on silver and copper surfaces will

a. Merals deposited onto cured polyimide surfaces

The polyimide substrates were prepared by spin coating polyamic acid onto a substrate followed by solvent extraction, imidization and curing at temperatures exceeding tion, imidization and curing at temperatures exceeding der ultra high vacuum conditions onto the polyimide films and their chemical interaction was followed by x-ray photoelectron spectroscopy /13-16,18-20,22, x-ray absorption fine structure (NEXAFS) measurements /14/, high resolution electron loss spectroscopy (HREELS) /17/ and recently also scanning electron tunneling microscopy /22/.

The first systematic XPS study on the interaction of evaporated metals with polyimide surfaces were published in 1984 by Chou and Tang /13/. They studied monolayers and submonolayers of Cr, Ni, Cu and Ag on freshly cured (T=350°C, 30 min) polyimide substrates. They concluded, that Cr and Ni react with the pendant oxygen in the substrate, whereas Cu and Ag are not forming chemical bonds. They also pr=sented a simple thermodynamic model to predict whether a given metal will form a chemical bond with the polymer during metallization at room temperature. According to this model Al, Mg, Mn, Sn, Ti and V should react with the pendant oxygen in polyimide.

Later experiments indicated that Cr /14/, Ti /15,16/ Al /17,18/ react with polyimide surfaces at coverages around and exceeding one monolayer under polymer bond cleavage and exceeding one monolayer under polymer bond cleavage and formation of metal oxides, carbides and nitrides. In the case of Cr /14,19/ and Al /18/ spectroscopic data suggest that the initial interaction between metal and polymer involves a charge transfer with the PWDA part of the polymer. Clabes et al. /14/ compared their XPS data for submonolayer coverages of Cr on PI with chemical and electrochemical reduced polyimide films. Reduction of FI involves electron transfer into the lowest unoccupied orbital (LUMO) of the PI which, according to calculations performed by Haight et al. /19/, has it's highest amplitude on the carbonyl carbon next nearest phenyl carbonyl oxygen atoms of two parallel PI-chains by charge donation yne the Cr atom initially interacts with two carbonyl oxygen atoms of two parallel PI-chains by charge donation into the LUMO of the PWDA parts of the PI macromolecules. A coordination with two adjacent ligands belonging to different monomer unit thus allows the chromium to reach the PMDA unit. is not possible through interaction with a single PMDA unit.

Supported by their "ab initio" calculations Haight et al. /19/ interpret their XPS data by a chromium/PMDA charge

for the Cr-atom is above the phenyl ring, analogous to a metal-x arene complex. The chemical shifts in the Cls, Ols and Nls spectra upon chromium deposition can be explained by theoretical calculation based on this model without invoking formation of covalent or ionic bonds. Support for this model also comes from the fact that the changes in ited, since chemical intuition would strongly argue against covalent bond formation with copper. Haight et al. also interpret the spectra taken for chromium coverages exceeding one monolayer without involving bond breaking in the the polyimide Cls, Ols, and Nls spectra are qualitatively the same irrespective whether chromium or copper is depostransfer complex where the most stable coordination polymer or compound formation.

mide films prepared by spin coating /21/ and by vapor deposition /22/ suggest that copper interacts via the imide part of the molecule and by chemical attack of the carbonyl groups. According to Mack et al. /22/ the interaction is stronger with vapor deposited PI surfaces than with the nyl groups. According to Mack et al. /22/ the interaction is stronger with vapor deposited PI surfaces than with the PI surfaces prepared by spin coating. Another bonding configuration where the copper interacts with the ODA part of the PI polymer was proposed by Sanda et al. /20/. Which of the models presented to describe the initial interaction between chromium and copper and polyimide surfaces remains However, recent experiments on copper deposition on polyiopen at this stage.

Interfactal chemistry of polyimide films on inor-

ganic substrates

polyimide on bulk copper and copper on polyimide is, despite the controversial models proposed for the chemical interaction, a well studied model system to demonstrate the differences in interfacial chemistry as a function of preparation method. In the following we will summarize the results for the PI/copper interfaces formed by (i) copper deposition on cured polyimide and (ii) spin coating of the polymer precursor polyamic acid (PAA) onto a copper film.

90° peal tests for (1) and (11). They found, that in case (11) adhesion is significantly enhanced as compared to copper deposited onto cured polyimide (1) and they attributed this to the difference in interfacial chemistry, i.e. ch.mical reaction between polyamic acid and bulk copper (1) as compared to copper atoms or clusters interacting with cured polyimide. The difference in interface chemistry was evident in cross sectional TEM observations (23). In the case of a sputter deposited copper film on a cured polyimide film, a sharp boundary was observed, whereas in the case of a polyimide/copper interface prepared by spin coating polyamic acid and subsequent interface prepared by cuprous oxide (Cu20) particles were found in the polymer matrix. Kim and coworkers /23/ measured the adhesion strength by

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polymer/substrate interface the polymer films have to be

That copper oxide particles are distributed over a thick-nets of -500 nm was recently reported by Burrell et al. /24/ for spun on polyimide films on copper. In their XPS and IR-Reflection Absorption measurements /24/ they at-

d the observed degradation and chemical modificarthe thick polyimide films to copper oxide particle formation/24/. tributed

films produced by uapor deposition (VD). However, if prince to imidization a drop of the solvent N-methylpyrrolidone is applied to a vapor deposited polyamic acid film, copper oxide particle formation in the polymer matrix can be observed by TEM (25/. The results of Kowalczyk et al. clearly show that the solvent provides mobility for the copper ions formed at the interface to diffuse into the polymer matrix and eventually react to cupreous oxide. Results on vapor deposited polyimide films on copper revealed that it is not possible to produce polyimide films of thickness less than 1 nm /26,27/. According to Kowalczyk et al./28/ this is due to incomplete imidization at the interface caused by carboxylate formation, whereas we believe /27/ that this is a consequence of fragmentation and loss of functional groups of the PMDA and ODA molecules in the interface. Both, the strong initial reaction of PMDA and ODA molecules in the interface, hoth, the copper surface, can provide an explanation for the dissolution of the copper surface and eventual cubreous oxide formation in the polspun-on polyimide films, Kowalczyk et al./25/ found no copper oxide particles in the polymer matrix in polyimide observations made by Kim et ymer matrix facilitated by the solvent. Contrary to the

nates poor adhesion is typically caused by cohesive failure in the polymer foil. As shown by a detailed XPS/IR/SEM study by Horn et al. /29/ a thin surface layer of the polymide foil facilitates the interface bond to the metalli tation layer, possibly via the edhesion promoters added to the polymer. Delamination leaves a thin polymer film on the metal, i.e. an adhesion between metal and polymer is stronger than cohesion in the polymer itself. If or to which extend copper cluster migration into the polymer as described above could cause cohesive failure is not known In commercially produced polyimide (Kapton®) /copper lamiat present. Relatively thick polyamic acid films were spun onto copper substrate by D.Y.Shih et al./30/. They followed the imidization and curing by sheet resistance, parallel plate capacitance measurements, FTIR and x-ray photoemission. Evidence for the interaction of copper with polyamic acid and that the amount of cuprous oxide found in the polymer matrix was significantly less when curing was performed in a reducing gas atmosphere as compared to nitrogen or vacuum curing. They concluded that Cu-lons are dissolved in the polyamic acid solvent layer in the initial curing stage for copper oxidation and degradation controlled by the supply of oxygen to the interface was obtained from FTIR and cross-sectional TEM i.icrographs. Shih et al. reported and subsequently diffuse into the polymer matrix.

For spectroscopic methods to be applied to analyze the

sufficiently thin. To prepare sufficiently thin polymer films by spin coating was only successful in a few cases. Russat /31/ reported results where polyamic acid dissolved in NMF was spun onto gold resulting in polyimide film thicknesses ranging between 1.3 to 2.9 nm after imidization and curing However, the interfacial reaction on gold could not be unambiguously established /31/.

Deposition of polyamic acid by coevaporation of the anhydride (PMDA) and the diamine (ODA) can provide sufficiently thin polyamic acid and, after curing, polyimide films to study the interfacial reaction with x-ray photoelectron spectroscopy /26-28, 32-37/, near edge x-ray absorption fine structure (NEXAFS) /28/ and infrared reflection absorption spectroscopy (IRAS)/36/. This vapor deposition preparation method to study the interfacial reactions has been applied by our group for copper /26,27/, silver /32-34/ and gold /37/ substrates and by Kowalczyk for Cu, Cr and Si surfaces /28/. The first description of the vapor phase preparation of polyimide films was given by Salem et al. 39/ for thick PI films (ds10µm). Application of UHV surface studies to such films was first described in reference/32/.

A detailed study of monomer adsorption (PMDA and ODA) interaction with clean silver surfaces /33/ showed that both molecules undergo partial fragmentation upon room temparature adsorption. Spectroscopic analysis of vapor deposited polyamic acid indicates that the reactive sites for the interaction with a silver substrate, as well as for vapor deposited groups in the molecule /37/. Evaporated gold atoms and cluster, are the amino carboxilic acid groups in the molecule /37/. Evaporated gold atoms and clusters preferentially interact via an electron transfer from the metal to the amino acid part of the molecule /37/. The interaction with a bulk silver surface is believed to involve silver carboxylate formation. A silver carboxylate bonding, either in a monodentate or biflection absorption experiments for the ultra-thin polyimide films obtained after curing the polyamic acid layers /33,37/. Such a salt-like ionic surface bond explains the sensitivity towards humidity, i.e it suggests that hydrolysilure.

There are strong similarities in the XPS and NEXAFS data for the case of PAA vapor deposited onto Cr surfaces and Cr evaporated onto cured polyimide surfaces /28/ suggesting that the same reactions occur in these differently prepared laminar structures. With the highly reactive chromium surfaces the formation of carbide, nitride and oxide species when the PAA/Cr interface is annealed was concluded from the XPS data. However, as discussed above, the XPS data for small and higher chromium coverages on cused polyimides are ambiguous with respect to chargetiansfer or covalent bond formation and fragmentation of the polymer.

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The results for PAA on a Si (III) 7x7 surface show a highly complex pattern, which can be explained by more than one geometric adsorption site, more than one functional group being involved in the bond formation, or a stepwise interaction pathway /28/. It is clear, however, that covalent bonds to the silicon substrate are formed in the polyamic acid state. No results have been published so far for curing experiments of vapor deposited polyamic acid state.

The results summarized above refer to studies related to the interfacial bond between polyimide films and the inorganic substrates. Typically delamination between polyimide and the substrate is, however, not caused by adhesive failure, but rather cohesive failure in the polymer itself. Although the effect of adhesion promoters (typically aminosilanes) in the formation of a strong interface bond have not been studied by spectroscopic techniques for polymide laminar structures, it is informative to recall the results obtained for a structural transition of the polymer between a polymer/metal interface and the polymer bulk.

XPS and IR data on silver led to the conclusion that at the surface the polymer chains are oriented away from the surface plane. This geometry is induced by the chemical bond to the surface /33,36/. Small angle x-ray scattering data by Russel /38/, however, proof that for thick polyimide films (d~ 75µm) the polyimide polymer chains in spunon films are oriented parallel to the surface plane. Such an orientation of the polymer chains with respect to the substrate was confirmed by IR absorption reflection studies for vapor deposited polyimide films (d>10nm) on copper /36/. At present it is not known at what distance away from the surface a transition between a nearly perpendicular to a parallel orientation relative to substrate plane of the polymer chains occurs, but it is tempting to speculate that such an orientational change in the polymer is related to the locus of failure in the case of cohesive

Conclusion

With their high temperature stability and easy processibility polyimide based polymers became an integral component in microelectronic device technology. Problems associated with adhesion in laminar structures have been mainly overcome by a careful control of process conditions, yet our understanding of the interfacial chemistry is still rudimentary and controversial. The application of spectroscopic techniques to identify the chemical composition and bonding at the interface has been established and is now routinely used in basic and applied research efforts. However, delamination typically occurs by cohesive failure in the polymer. To identify the locus and chemical and/or physical mechanism of cohesive failure re-

mains a challenge for future research.

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An excellent overview on the adhesion of polyimides to metal and ceramic surfaces including a summary on adhesion theories and adhesion measurements, by L.P. Buchwalter, came to the attention of the author. This review will appear in the Journal of Adhesion Science and Technology.

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